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MOS Integrated Circuit $\mu PD78P328$

16/8-BIT SINGLE-CHIP MICROCONTROLLER

The μ PD78P328 is a product provided by replacing the μ PD75328's internal mask ROM with one-time PROM or EPROM.

The one-time PROM version is programmable only once and is useful for small-lot production of many different products and early development and time-to-market of application sets.

The EPROM version is reprogrammable, and suited for the evaluation of systems.

Functions are described in detail in the following user's manual. Be sure to read it before designing. μ PD78328 User's Manual: IEU-1268

FEATURES

- μPD78328 compatible
 - For mass-production, the μPD78P328 can be replaced with the μPD78328 incorporating mask ROM
- Internal PROM: 16,384 x 8 bits
 - Programmable once only (one-time PROM version without window)
 - Erasable with ultraviolet rays and electrically programmable (EPROM version with window)
- PROM programming characteristics: μPD27C256A compatible
- The $\mu PD78P328$ is a QTOPTM microcontroller.

Remark QTOP microcontroller is a general term for microcontrollers which incorporates one-time PROM, and are totally supported by NEC's programming service (from programming to marking, screening, and verification).

ORDERING INFORMATION

Part Number	Package	Internal ROM	_
μ PD78P328CW	64-pin plastic shrink DIP (750 mils)	One-time PROM	
μ PD78P328GF-3BE	64-pin plastic QFP (14 x 20 mm)	One-time PROM	
μPD78P328DW	64-pin ceramic shrink DIP (750 mils) (with window)	EPROM	

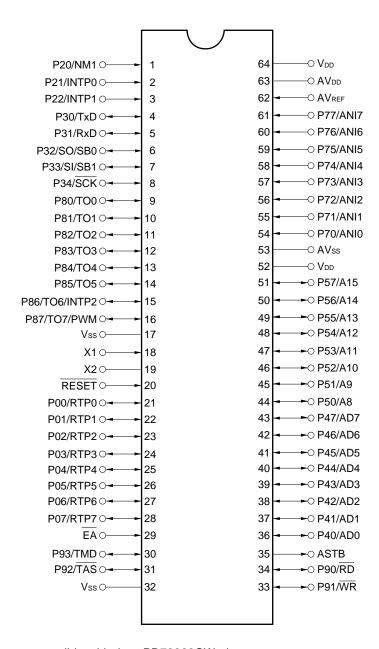
Functions common to the one-time PROM and EPROM versions are referred to as PROM functions throughout this document.

The information in this document is subject to change without notice.



PIN CONFIGURATIONS

- (1) Normal operating mode
- 64-pin plastic shrink DIP (750 mils) μ PD78P328CW
- 64-pin ceramic shrink DIP (750 mils) (with window) μ PD78P328DW

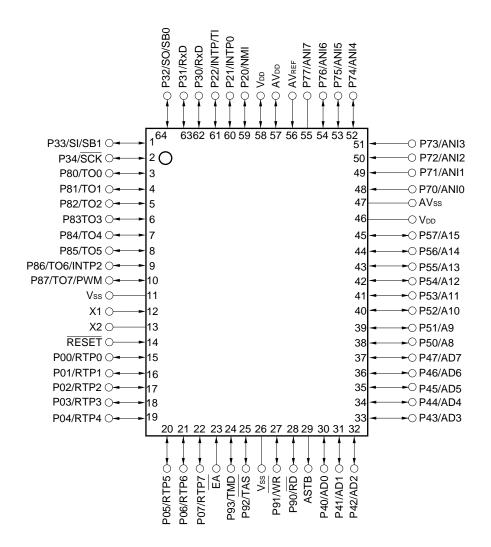


Remark These pins are compatible with the μ PD78328CW pins.



• 64-pin plastic QFP (14 x 20 mm)

 μ PD78P328GF-3BE



Remark These pins are compatible with the μ PD78328GF pins.



P00-P07 : Port 0 SI : Serial Input SO P20-P22 : Port 2 : Serial Output P30-P34 : Port 3 SB0-SB1 : Serial Bus0-1 P40-P47 : Port 4 RD Read Strobe WR : Port 5 : Write Strobe P50-P57 : Port 7 **ASTB** : Address Strobe P70-P77 : Port 8 EΑ **External Access** P80-P87 : Port 9 RESET : Reset P90-P93

A8-A15 : Address8-15 SCK : Serial Clock

AD0-AD7 : Address0-7/Data0-7 TAS : Turbo Access Strobe
ANI0-ANI7 : Analog Input0-7 TMD : Turbo Mode

TO0-TO7 : Timer Output0-7 X1, X2 : Crystal1, 2
NMI : Nonmaskable Interrupt AVDD : Analog VDD

PWM : Pulse Wide Modulation Output AVREF : Analog Reference Voltage

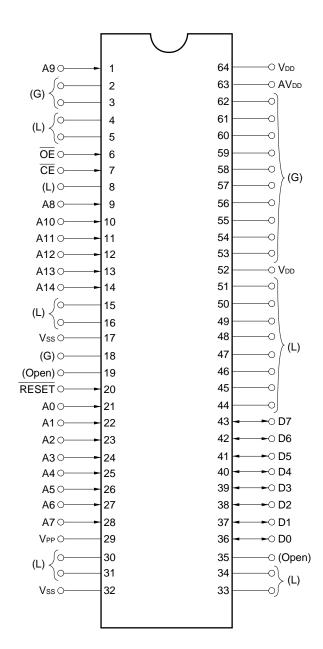
INTP0-INTP2 : Interrupt From Peripherals0-2 AVss : Analog Vss RTP0-RTP7 : Real-Time Port0-7 Vpd : Power Supply TxD : Transmit Data Vss : Ground

RxD : Receive Data





- (2) PROM programming mode ($\overline{RESET} = H$, AVDD = L)
- 64-pin plastic shrink DIP (750 mils) μ PD78P328CW
- 64-pin ceramic shrink DIP (750 mils) (with window) μPD78P328DW



Caution The recommended connection of the unused pins in the PROM programming mode are indicated in parentheses.

L : Connect each pin to Vss via a resistor.

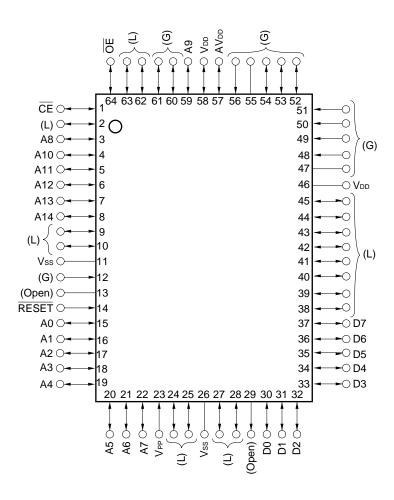
G : Connect the pin to Vss.

Open : Leave the pin unconnected.



• 64-pin plastic QFP (14 x 20 mm)

 μ PD78P328GF-3BE



Caution The recommended connection of the unused pins in the PROM programming mode are indicated in parentheses.

L : Connect each pin to Vss via a resistor.

G : Connect the pin to Vss.

Open : Leave the pin unconnected.

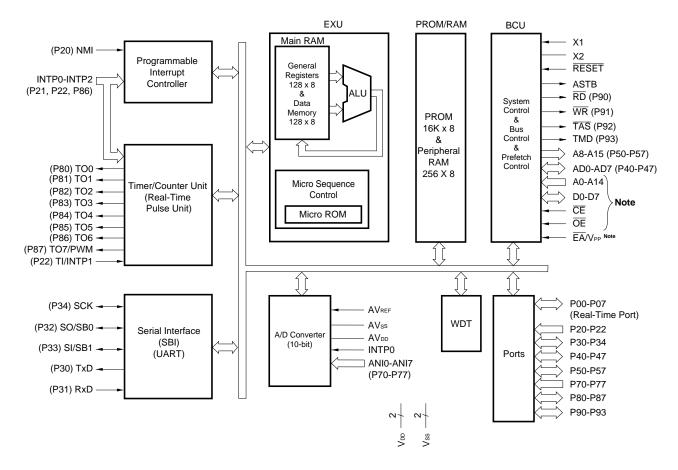
A0-A14 : Address0-14 AVDD : Analog VDD D0-D7 : Data0-7 VDD : Power Supply $\overline{\text{CE}}$: Chip Enable Vss : Ground

OE : Output Enable VPP : Programming Power Supply

RESET : Reset



BLOCK DIAGRAM



Note During PROM programming mode





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1. PIN FUNCTIONS

1.1 Normal Operating Mode

(1) Port Pins

Pin Name	Input/Output	Function	Alternate
			Function
P00-P07	Input/Output	PORT0	RTP0-RTP7
		4-/8-bit input/output port	
		Input or output mode can be specified bit-wise.	
		The port can also operate as a real-time output port.	
P20	Input	PORT 2	NMI
P21		3-bit input-only port	INTP0
P22			INTP1/TI
P30	Input/Output	PORT 3	TxD
P31		5-bit input/output port	RxD
P32		Input or output mode can be specified bit-wise.	SO/SB0
P33			SI/SB1
P34			SCK
P40-P47	Input/Output	PORT 4	AD0-AD7
		8-bit input/output port	
		Input or output mode can be specified in 8-bit units.	
P50-P57	Input/Output	PORT 5	A8-A15
		8-bit input/output port	
		Input or output mode can be specified bit-wise.	
P70-P77	Input	PORT 7	ANI0-ANI7
		8-bit input-only port	
P80	Input/Output	PORT 8	TO0
P81		8-bit input/output port	TO1
P82		Input or output mode can be specified bit-wise.	TO2
P83			TO3
P84			TO4
P85			TO5
P86			TO6/INTP2
P87			TO7/PWM
P90	Input/Output	PORT 9	RD
P91		4-bit input/output port	WR
P92		Input or output mode can be specified bit-wise.	TAS
P93			TMD





(2) Non-Port Pins (1/2)

Pin Name	Input/Output	Function	Alternate
			Function
RTP0-RTP7	Output	Real-time output port which outputs a pulse in synchronization with the trigger signal from	P00-P07
		real-time pulse unit (RPU).	
NMI	Input	Edge-detected nonmaskable interrupt request input.	P20
		The rising or falling edge can be selected for the valid edge by setting the mode register.	
INTP0	Input	Edge-detected external interrupt request input.	P21
INTP1		The valid edge can be specified in the mode register.	P22/T1
INTP2			P86/TO6
TI	Input	External count clock input pin to timer 1 (TM1).	S22/INTP1
RxD	Input	Serial data input pin to asynchronous serial interface (UART).	P30
TxD	Output	Serial data output pin from asynchronous serial interface (UART).	P31
SO	Output	Serial data output pin from clocked serial interface in 3-wire mode.	P32/SB0
SI	Input	Serial data input pin to clocked serial interface in 3-wire mode.	P33/SB1
SB0	Input/Output	Serial data input/output pins to/from clocked serial interface in SBI mode.	P32/SO
SB1			P33/SI
SCK	Input/Output	Serial clock input/output pin to/from clocked serial interface.	P34
AD0-AD7	Input/Output	Multiplexed address/data bus used when external memory is added.	P40-P47
A8-A15	Output	Address bus used when external memory is added.	P50-P57
TO0	Output	Pulse output from real-time pulse unit.	P80
TO1			P81
TO2			P82
TO3			P83
TO4			P84
TO5			P85
TO6			P86/INTP2
TO7			P87/PWM
PWM	Output	PWM signal output from real-time pulse unit.	P87/TO7
RD	Output	Strobe signal output for external memory read operation.	P90
WR		Strobe signal output for external memory write operation.	P91
TAS		Control signal output pins to access turbo access manager (µPD71P301). Note	P92
TMD			P93
ASTB	Output	Timing signal output pin to externally latch an address information output to port 4 for	_
		external memory access.	
EΑ	Input	For μ PD78P328, normally connect the \overline{EA} pin to V_{DD} . When the \overline{EA} pin is connected to	_
		$V_{\rm SS}$, the μ PD78P328 enters the ROMless mode and external memory is accessed.	
		The \overline{EA} pin level cannot be changed during operation.	

Note Turbo access manager (μ PD71P301) is available for maintenance purposes only.





(2) Non-Port Pins (2/2)

Pin Name	Input/Output	Function	Alternate
			Function
ANI0-ANI7	Input	Analog input to A/D converter.	P70-P77
AVREF	Input	A/D converter reference voltage input.	_
AV _{DD}	_	A/D converter analog power supply.	_
AVss	_	A/D converter GND.	_
RESET	Input	System reset input.	_
X1	Input	Crystal connection pin for system clock generation. To supply external clock,	_
X2	_	input to the X1 and input reverse signal to the X2 pin (X2 pin can be unconnected.)	_
V _{DD}	_	Positive power supply pin.	_
Vss	_	GND pin.	_

1.2 PROM Programming Mode (RESET = H, AVDD = L)

Pin Name	Input/Output	Function
AVDD	Input	PROM programming mode setting.
RESET	RESET	
A0-A14 — Address bus.		Address bus.
D0-D7	_	Data bus.
CE	Input	PROM enable to PROM.
ŌĒ	Input	Read strobe to PROM.
V _{PP}	_	Write power supply.
V _{DD}		Positive power supply.
Vss		GND.





1.3 Pin Input/Output Circuits and Recommended Connection of Unused Pins

Table 1-1 and Figure 1-1 show the pin input/output circuit schematically.

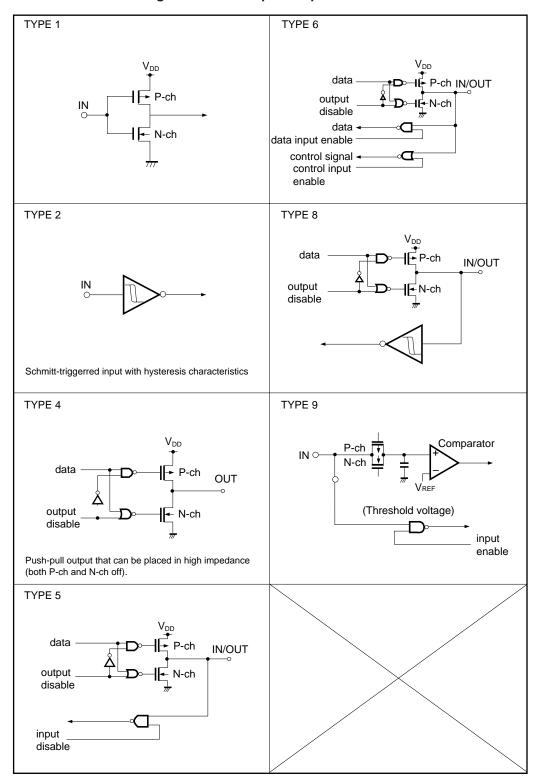
Table 1-1. Pin Input/Output Circuits and Recommended Connection of Unused Pins

Pin	Input/Output circuit type	Recommended connection of unused pins
P00P07/RTP0-RTP7	5	Input state: Independently connect to VDD or Vss via a resistor.
		Output state: Leave Open.
P21/NMI	2	Connect to Vss.
P21/INTP0		
P27/INTP6/TI		
P30/TxD	5	Input state: Independently connect to VDD or Vss via a resistor.
P31/RxD		Output state: Leave Open.
P32/SO/SB0	8	
P33/SI/SB1		
P34/SCK		
P40/AD0-P47/AD0-AD7	5	
P50/P57/A8-A15		
P70-P77/ANI0-ANI7	9	Connect to Vss.
P80-P85/TO0-TO5	5	Input state: Independently connect to V _{DD} or V _{SS} via a resistor.
P86/TO6/INTP2	6	Output state: Leave Open.
P87/TO7/PWM	5	
P90/RD	5	
P91/WR		
P92/TAS		
P93/TMD		
ASTB	4	Leave Open.
EA	1	_
RESET	2	_
AVREF, AVSS	_	Connect to Vss.
V _{DD}	_	Connect to VDD.





Figure 1-1. Pin Input/Output Circuits





2. DIFFERENCES BETWEEN μ PD78P328 and μ PD78328

The μ PD78P328 is a product provided by replacing the μ PD78328's on-chip mask ROM with one-time PROM or EPROM. Thus, the μ PD78P328 and μ PD78328 are the same in function except for the ROM specifications such as write or verify. Table 2-1 lists the differences between these two products.

This Data Sheet describes the PROM specification function. Refer to the μ PD78328 documents for details of other functions.

Table 2-1. Differences between μ PD78P328 and μ PD78328

Item	μ PD78P328	μ PD78P328		
Internal program memory	One-time PROM	EPROM	Mask ROM	
(electrical program)	(programmable only once)	(reprogrammable)	(nonprogrammable)	
PROM programming pin	Contained	Contained		
Package	64-pin plastic shrink DIP	64-pin ceramic shrink DIP	64-pin plastic shrink DIP	
	64-pin plastic QFP	• 64-pin plastic QFP (with window)		
Electrical specifications	Current dissipations are differen	nt.		
Others	Noise immunity and noise radia	Noise immunity and noise radiation differ because circuit comple		
	different.			

* Caution The noise immunity and noise radiation differ between the PROM and mask ROM versions. To replace the PROM version with the mask ROM version when shifting from experimental production to mass production, evaluate your system by using the CS version (not ES version) of the mask ROM version.

*





3. PROM PROGRAMMING

The PROM incorporated in the μ PD78P328 is a 16,384 x 8-bit electrically writable PROM. For programming, set the PROM programming mode by using the $\overline{\text{RESET}}$ and AV_{DD} pins.

The programming characteristics are compatible with the μ PD27C256A programming characteristics.

Table 3-1. Pin Function in Programming Mode

Function	Normal Operating Mode	Programming Mode
Address input	P00-P07, P80, P20, P81-P85	A0-A14
Data input	P40-P47	D0-D7
Chip enable/program pulse	P33	CE
Output enable	P32	ŌĒ
Program voltage	ĒĀ	VPP
Mode control	RESET, AVDD	

3.1 Operation Mode

To set the program write/verify mode, set $\overline{RESET} = H$ and AVDD = L. For the mode, the operation mode can be selected by setting the \overline{CE} and \overline{OE} pins, as listed in Table 3-2.

To read the PROM contents, set the read mode.

Connect the unused pins exactly as indicated on Pin Configuration.

Table 3-2. PROM Programming Operation Mode

Mode	RESET	AV _{DD}	CE	ŌE	V _{PP}	V _{DD}	D0-D7
Program write	Н	L	L	Н	+12.5 V	+6 V	Data input
Program verify			Н	L			Data output
Program inhibit	1		Н	Н	-		High impedance
Read	1		L	L	+5 V	+5 V	Data output
Output disable			L	Н			High impedance
Standby			Н	L/H	-		High impedance

Caution When V_{PP} is set to +12.5 V and V_{DD} is set to +6V, setting both \overline{CE} and \overline{OE} to L is inhibited.





3.2 PROM Write Procedure

The write procedure into PROM is as follows: (See also Figure 3-2).

- (1) Fix RESET = H and AVDD = L. Connect other unused pins exactly as indicated in section "Pin Configuration."
- (2) Supply +6 V to the VDD and +12.5 V to the VPP pin.
- (3) Supply an initial address.
- (4) Supply write data.
- (5) Supply 1 ms program pulse (active low) to the \overline{CE} pin.
- (6) Execute the verify mode. Check whether or not the write data is written normally.
 - When it is written normally: Proceed to step (8).
 - When it is not written normally: Repeat steps (4) to (6).

If the data is not written normally after 25 repetitions of the steps, proceed to step (7).

- (7) Assume the device to be defective. Stop write operation.
- (8) Supply write data and X (number of steps (4) to (6) repetitions) x 3 ms program pulses (additional write).
- (9) Increment the address.
- (10) Repeat steps (4) to (9) to the last address.

Figure 3-1 shows the PROM Write/Verify Timing Steps (2) to (8) above.

Figure 3-1. PROM Write/Verify Timing

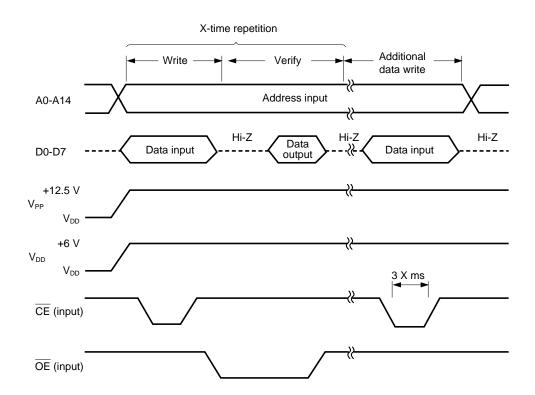
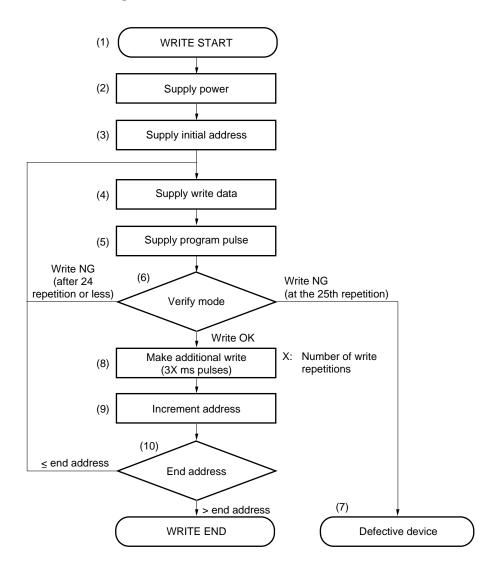


Figure 3-2. Write Procedure Flowchart







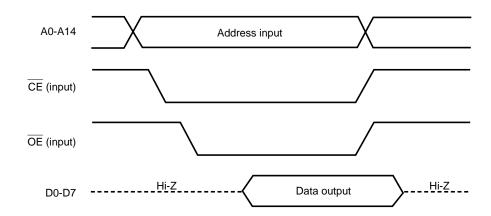
3.3 PROM Read Procedure

The read procedure of the PROM contents into the external data bus (D0-D7) is as follows.

- (1) Fix $\overline{RESET} = H$ and AVDD = L. Connect other unused pins exactly as indicated on Pin Configuration.
- (2) Supply +5 V to the VDD and VPP pins.
- (3) Input the address of the data to be read to the A0-A14 pins.
- (4) Execute the read mode.
- (5) The data is output to the D0-D7 pins.

Figure 3-3 shows the PROM read timing steps (2) to (5) above.

Figure 3-3. PROM Read Timing







4. ERASURE CHARACTERISTICS (EPROM VERSION ONLY)

The data written into the μ PD78P328DW program memory can be erased (FFH) and new data can be rewritten into the memory.

To erase data, apply light with a wave length shorter than 400 nm to the window. Normally, apply ultraviolet rays having the 254-nm wave length. The radiation amount required to completely erase data is as follows:

- Ultraviolet strength x erasure time: 15 W•s/cm² or more
- Erasure time: 15 to 20 minutes when a 12,000 μ W/cm² ultraviolet lamp is used. However, the time may be prolonged due to ultraviolet lamp performance deterioration, dirty window, etc.

For erasure, place an ultraviolet lamp at a position within 2.5 cm from the window. If a filter is attached to the ultraviolet lamp, remove the filter before applying ultraviolet rays.

5. WINDOW SEAL (EPROM VERSION ONLY)

If the μ PD78P328DW window is exposed to sunlight or fluorescent lamp light for hours, EPROM data may be erased and the internal circuit may operate erroneously. To prevent such accidents from occurring, put a protective seal on the window.

A protective seal whose quality is guaranteed by NEC is attached to every EPROM version with window at shipment.

6. ONE-TIME PROM VERSION SCREENING

The one-time PROM versions (μ PD78P328CW, 78P328GF-3BE) cannot be completely tested by NEC for shipment because of their structure. For screening, it is recommended to verify PROM after storing the necessary data under the following conditions:

NEC provides chargeable services ranging from one-time PROM writing to marking, screening, and verification for QTOP microcontroller products. For details, contact an NEC sales representative.

Storage temperature	Storage time
125°C	24 hours





7. ELECTRICAL SPECIFICATIONS

Absolute Maximum Ratings (TA = 25 °C)

Parameter	Symbol	Test Condit	tions	Ratings	Unit
Power supply voltage	V _{DD}			-0.5 to +7.0	V
	V _{DD}			-0.5 to V _{DD} +0.5	V
	V _{PP}			-0.5 to +13.5	V
	AVss			-0.5 to +0.5	V
Input voltage	Vıı	Note 1		-0.5 to V _{DD} +0.5	V
	V _{I2}	P20/NIM (A	(9) PIN	-0.5 to +13.5	V
Output voltage	Vo			-0.5 to V _{DD} +0.5	V
Output current, low	Іоь	All output pins Total for all pins		4.0	mA
				90	mA
Output current, high	Іон	All output p	ins	-1.0	mA
		Total for all pins		-20	mA
Analog input voltage	VIAN	Note 2	AVDD > VDD	-0.5 to V _{DD} +0.5	V
			$V_{DD} \ge AV_{DD}$	-0.5 to AV _{DD} +0.5	V
A/D converter reference	AVREF		AVDD > VDD	-0.5 to V _{DD} +0.3	V
input voltage			$V_{DD} \ge AV_{DD}$	-0.5 to AV _{DD} +0.3	V
Operating ambient temperature	TA			-10 to +70	°C
Storage temperature	Tstg			-65 to +150	°C

Notes 1. Pins except for P20/NMI (A9), P70/ANI0-P77/ANI7

2. P70/ANI0-P77/ANI7

* Caution Product quality may suffer if the absolute maximum rating is exceeded for even a single parameter, even momentarily. In other words, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions which ensure that the absolute maximum ratings are not exceeded.

Recommended Operation Conditions

Oscillation frequency	TA	VDD
8 MHz ≤ fxx ≤ 16 MHz	-10 to +70 °C	+5.0 V ±5%

Capacitance (TA = 25 °C, Vss = VDD = 0 V)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Input capacitance	Cı	f = 1 MHz			10	pF
Output capacitance	Со	Unmeasured pins returned to 0 V			20	pF
I/O capacitance	Сю				20	pF





Oscillator Characteristics (TA = -10 to +70 °C, VDD = +5 V $\pm 5\%$, Vss = 0 V)

Resonator	Recommended Circuit	Parameter	MIN.	MAX.	Unit
Ceramic or crystal resonator	X2 X1 V _{ss} — C2 — C1	Oscillation frequency (fxx)	8	16	MHz
External clock	X1 X2 HCMOS Inverter or	X1 input frequency (fx)	8	16	MHz
	X1 X2 Open	X1 input rise, fall time (fxR, txr)	0	20	ns
	HCMOS Inverter	X1 input high, low level width (twxH, twxL)	25	80	ns

Caution When using the system clock oscillator, wire the portion enclosed in dotted line in the figure as follows to avoid adverse influences on the wiring capacitance:

- · Keep the wiring length as short as possible.
- Do not cross the wiring over the other signal lines. Do not route the wiring in the vicinity of lines through which a high fluctuating current flows.
- Always keep the ground point of the capacitor of the oscillator circuit at the same potential as
 Vss. Do not connect the power source pattern through which a high current flows.
- Do not extract signals from the oscillation circuit.

Recommended Oscillator Constants

Ceramic resonator

Manufacturer Name	Part Number	Frequency	Recommer	nded
		[MHz]	Constants	
			C1 [pF]	C2 [pF]
MURATA	CSA8.00MT	8.0	30	30
	CSA12.0MT	12.0		
	CSA16.00MX040	16.0	15	15
	CST8.00MTW	8.0	Internal	Internal
	CST12.00MTW	12.0		
	CST16.00MXW0C3	16.0		





DC Characteristics (TA = -10 to +70 °C, VDD = +5 V $\pm 5\%$, Vss = 0 V)

Parameter	Symbol	Test Condition	S	MIN.	TYP.	MAX.	Unit
Input voltage, low	VIL			0		0.8	V
Input voltage, high	V _{IH1}	Note 1		2.2			V
	V _{IH2}	Note 2		0.8V _{DD}			
Output voltage, low	Vol	IoL = 2.0 mA				0.45	V
Output voltage, high	Vон	Іон = -400 μΑ	Іон = -400 μΑ				V
Input leakage current	Li	$0 \text{ V} \leq V_{I} \leq V_{DD}$				±10	μΑ
Output leakage current	ILO	$0 \text{ V} \leq \text{Vo} \leq \text{Vpd}$				±10	μΑ
V _{DD} power supply current	I _{DD1}	Operation mod	e		45	75	mA
	I _{DD2}	HALT mode			25	45	mA
Data retention voltage	VDDDR	STOP mode		2.5			V
Data retention current	IDDDR	STOP mode	VDDDR = 2.5 V		3	15	μΑ
			VDDDR = 5.0 V ±5%		10	50	μΑ

- Notes 1. Pins except for RESET, X1, X2, P20/NMI, P21/INTP0, P22/INTP1/TI, P86/INTP2/T00, P32/S0/SB0, P33/SI/SB1, or P34/SCK.
 - **2.** RESET, X1, X2, P20/NMI, P21/INTP0, P22/INTP1/TI, P86/INTP2/T00, P32/S0/SB0, P33/SI/SB1, or P34/SCK pins.





AC Characteristics (TA = -10 to +70 °C, VDD = +5 V $\pm 5\%$, Vss = 0 V)

Discontinuous read/write operation (when general-purpose memory is connected)

Parameter	Symbol	Test Conditions	MIN.	MAX.	Unit
System clock cycle time	tсүк		125	250	ns
Address setup time (to ASTB \downarrow)	tsast		22		ns
Address hold time (from ASTB \downarrow)	thsta		32		ns
$Address \to \overline{RD} \downarrow delay \ time$	tdar		85		ns
$\overline{RD}\downarrow o$ address float time	tFRA			8	ns
$Address \to data \ input\ time$	tDAID			222	ns
$\overline{ m RD} \downarrow ightarrow$ data input time	torid			112	ns
$ASTB \downarrow \to \overline{RD} \downarrow delay\ time$	tostr		42		ns
Data hold time (from RD ↑)	thrid		0		ns
$\overline{RD} \uparrow \to address \ active \ time$	tdra		37		ns
RD low-level width	twrL		147		ns
ASTB high-level width	twsтн		37		ns
$Address \to \overline{WR} \downarrow delay \ time$	tdaw		85		ns
ASTB \downarrow \rightarrow data output time	tostod			102	ns
$WR\downarrow o data$ output time	towod			40	ns
$ASTB \downarrow \to \overline{WR} \downarrow delay \ time$	tostw		42		ns
Data setup time (to WR ↑)	tsodw		137		ns
Data hold time (from WR ↑)	thwod		32		ns
$\overline{ m WR} \uparrow ightarrow m ASTB \downarrow m delay time$	towst		42		ns
WR low-level width	twwL		147		ns





tcүк-Dependent Bus Timings

Parameter	Calculation expression	MIN./MAX.	Unit
tsast	0.5T – 40	MIN.	ns
thsta	0.5T - 30	MIN.	ns
tdar	T – 40	MIN.	ns
tdaid	(2.5 + n) T – 90	MAX.	ns
torio	(1.5 + n) T – 75	MAX.	ns
tostr	0.5T – 20	MIN.	ns
tdra	0.5T – 25	MIN.	ns
twrL	(1.5 + n) T – 40	MIN.	ns
twsтн	0.5T – 25	MIN.	ns
tdaw	T – 40	MIN.	ns
tostod	0.5T + 40	MAX.	ns
tostw	0.5T – 20	MIN.	ns
tsodw	1.5T – 50	MIN.	ns
thwod	0.5T - 30	MIN.	ns
towst	0.5T – 20	MIN.	ns
twwL	(1.5 + n) T – 40	MIN.	ns

Remarks 1. T = tcyk = 1/fck (fck is the internal system clock frequency and is provided by dividing fxx or fx by two).

- 2. n is the number of wait cycles defined by user software.
- 3. Only parameters listed in the table are dependent on $tcy\kappa$.





Serial Operation (TA = -10 to +70 °C, VDD = +5 V $\pm 5\%$, Vss = 0 V)

Parameter	Symbol	Test Condition	ns	MIN.	MAX.	Unit
Serial clock cycle time	tcysk	Input	External clock	1		μs
		Output	Internal divide by 8	8T		tcyk
			Internal divide by 32	32T		tcyĸ
Serial clock high-level width	twskL	Input	External clock	420		ns
		Output	Internal divide by 8	4T-80		ns
			Internal divide by 32	16T-100		ns
Serial clock high-level width	twsĸн	Input	External clock	420		ns
		Output	Internal divide by 8	4T-80		ns
			Internal divide by 32	16T-100		ns
SI setup time (to $\overline{SCK} \uparrow$)	tsrxsk			80		ns
SI hold time (from $\overline{\text{SCK}} \uparrow$)	thskrx			80		ns
SO/SB0, SI/SB1	tDSBSK1	CMOS push-p	oull output	0	210	ns
output delay time (from $\overline{SCK} \downarrow$)		(3-wire serial	I/O mode)			
	tDSBSK2	Open drain ou	ıtput	0	600	ns
		(SBI mode), R	$RL = 1 k\Omega$			
SB0, SB1 high hold time (from $\overline{\text{SCK}} \uparrow$)	tнsвsк	SBI mode		4T		tcyk
SB0, SB1 low setup time (from $\overline{SCK} \downarrow$)	tssbsk			4T		tcyk
SB0, SB1 low-level width	twsBL			4T-20		ns
SB0, SB1 high-level width	twbsh			4T-20		ns

Remark T = tcyk = 1/fck (fck is the internal system clock frequency and is provided by dividing fxx or fx by two.)





Other operations (TA = -10 to +70°C, VDD = +5 V ± 5 %, Vss = 0 V)

Parameter	Symbol	Test Conditions	MIN.	MAX.	Unit
NMI high-, low-level widths	twnih,		5		μs
	twnil				
INTP0 high-, low-level widths	twiон,		8T		tcyk
	twioL				
INTP1 high-, low-level widths	twi1H,		8T		tсүк
	twi1L				
INTP2 high-, low-level widths	twi2H,		8T		tcyk
	twi2L				
RESET high-, low-level widths	twrsh,		5		μs
	twrsL				
TI high-, low-level widths	twrin,	TM1	8T		t cyk
	twTIL	In the event counter mode			

Remark T = tcyk = 1/fclk (fclk is the internal system clock frequency and is provided by dividing fxx or fx by two.)

External clock timing (Ta = -10 to $+70^{\circ}$ C, VDD = +5 V $\pm 5\%$, Vss = 0 V)

Parameter	Symbol	Test Conditions	MIN.	MAX.	Unit
X1 input high-, low-level widths	twxH,		25	80	ns
	twxL				
X1 input rise, fall times	txR,		0	20	ns
	txF				
TI input cycle time	tcyk		62	125	ns





A/D Converter (TA = -10 to +70°C, VDD = +5 V ± 5 %, Vss = AVss = 0 V, VDD -0.5 V \leq AVDD \leq VDD)

Parameter	Symbol	Test Condition	S	MIN.	TYP.	MAX.	Unit
Resolution							bit
Total error Note1		4.5 V ≤ AVREF	≤ AV _{DD}			±0.4	%FSR
		3.4 V ≤ AVREF	≤ AV _{DD}			±0.7	%FSR
Quantification error						±1/2	LSB
Conversion time	tconv			144			tcyĸ
Sampling time	tsamp			24			tcyk
Zero scale error Note1		4.5 V ≤ AVREF :	4.5 V ≤ AVREF ≤ AVDD		+1.5	±2.5	LSB
		3.4 V ≤ AVREF	≤ AV _{DD}		+1.5	±4.5	LSB
Fullscale error Note1		4.5 V ≤ AVREF :	≤ AV _{DD}		+1.5	±2.5	LSB
		3.4 V ≤ AVREF :	≤ AV _{DD}		+1.5	±4.5	LSB
Nonlinear error Note1		4.5 V ≤ AVREF :	≤ AV _{DD}		+1.5	±2.5	LSB
		3.4 V ≤ AVREF	≤ AV _{DD}		+1.5	±4.5	LSB
Analog input voltage Note2	VIAN			-0.3		AV _{DD}	V
Basic voltage	AVREF			3.4		AVDD	V
AVREF current	Alref				1.0	3.0	mA
AV _{DD} supply current	Aldd				2.0	6.0	mA
A/D converter data	Aldddr	STOP mode	AVDDDR = 2.5 V		2.0	10	μΑ
retention current			AVDDDR = 5 V±5%		10	50	μΑ

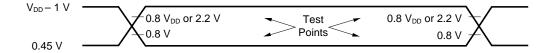
Notes 1. Quantization error is excluded.

2. When $-0.3~V \le V_{IAN} \le 0~V$, conversion result is 000H. When $0~V < V_{IAN} < AV_{REF}$, conversion is executed by 10-bit resolution. When $AV_{REF} \le V_{IAN} \le AV_{DD}$, conversion result is 3 FFH.

Standby flag retention characteristics ($TA = -10^{\circ}C$ to $70^{\circ}C$)

Parameter	Symbol	Test Conditions	MIN.	MAX.	Unit
Standby flag retention power supply voltage	VDDDR		2.5	5.5	V
V _{DD} rising, falling time	trvd,		200		ns
	trvd				

AC Timing Test Points

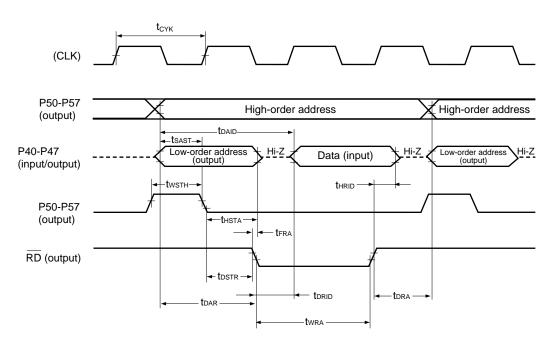




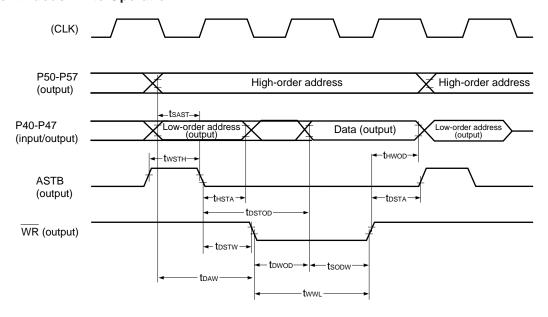


Timing Wave Forms

Discontinuous Read Operation



Discontinuous Write Operation

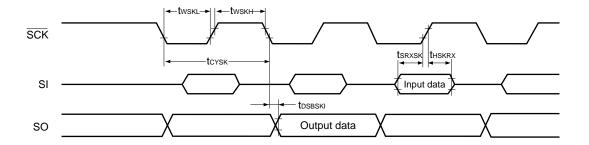






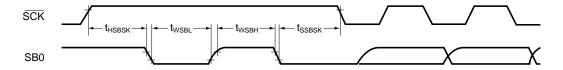
Serial Operation

Three-Wire Serial I/O Mode:

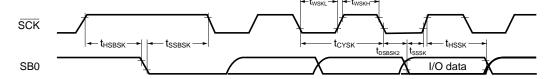


SBI Mode

Bus Release Signal Transfer



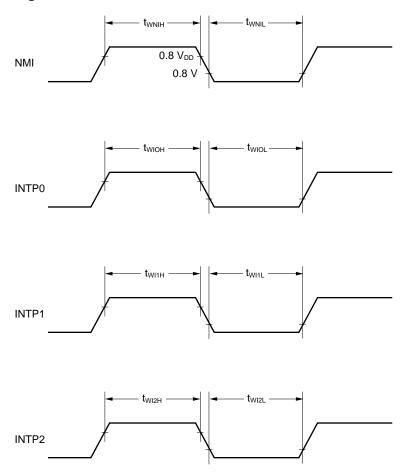
Command Signal Transfer



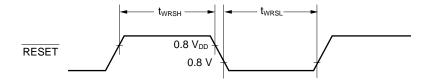




Interrupt Input Timing



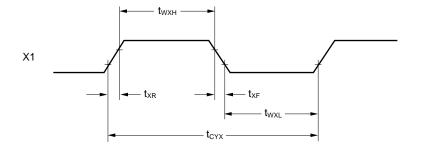
Reset Input Timing



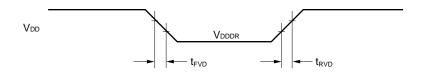




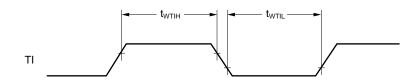
External Clock Timing



Standby Flag Retention Timing



TI Pin Input Timing







DC Programming Characteristics (TA = 25 ± 5 °C, Vss = 0 V)

Parameter	Symbol	Symbol	Test conditions	MIN.	TYP.	MAX.	Unit
		Note1					
Input voltage, high	VIH	VIH		2.2		VDDP	V
						+0.3	
Input voltage, low	VIL	VIL		-0.3		0.8	V
Input leakage current	ILIP	Li	$0 \le V_1 \le V_{DDP}$ Note 2			±10	μΑ
Output voltage, high	Vон	Vон	I он = $-400 \mu A$	2.4			V
Output voltage, low	Vol	Vol	IoL = 2.0 mA			0.45	V
Input current	I _{A9}	_	A9 (P20/NMI) pin			±10	μΑ
Output leakage current	ILO	_	$0 \le V_0 \le V_{DDP}, \overline{OE} = V_{IN}$			10	μΑ
PROG pin high voltage input	IIP	_				±10	μΑ
current							
V _{DDP} power supply voltage	VDDP	V _{DD}	Program memory write mode	5.75	6.0	6.25	V
			Program memory read mode	4.5	5.0	5.5	V
VPP power supply voltage	VPP	VPP	Program memory write mode	12.2	12.5	12.8	V
			Program memory read mode	VPP = V	PP = VDDP		V
VDDP power supply current	IDD	IDD	Program memory write mode		10	30	mA
			Program memory read mode		10	30	mA
			$\overline{CE} = V_IL,OE = V_IN$				
VPP power supply current	IPP	IPP	Program memory write mode		10	30	mA
			$\overline{CE} = V_{IL}, \overline{OE} = V_{IN}$				
			Program memory read mode		1	100	μΑ

Notes 1. Corresponding μ PD27C256A symbols.

2. VDDP is VDD pin during the programming mode.





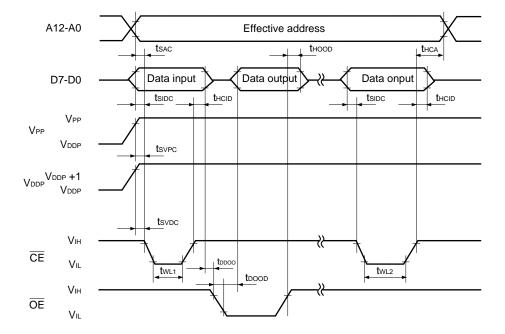
AC Programming Characteristics (TA = 25 \pm 5 $^{\circ}$ C, Vss = 0 V)

Parameter	Symbol	Symbol	Test conditions	MIN.	TYP.	MAX.	Unit
		Note					
Address setup time (to $\overline{\sf CE}\ \downarrow$)	tsac	tas		2			μs
$Data o \overline{OE} \downarrow delay time$	todoo	toes		2			μs
Input data setup time (to CE ↓)	tsidc	tos		2			μs
Address hold time (from CE ↑)	thca	tah		2			μs
Input data hold time (from CE ↑)	thcid	tон		2			μs
Output data hold time (from OE 1)	tноор	tor		0		130	ns
V _{PP} setup time (to $\overline{\text{CE}}$ ↓)	tsvpc	tvps		2			μs
V _{DDP} setup time (to $\overline{\text{CE}}$ ↓)	tsvdc	tvps		2			μs
Initial program pulse width	twL1	tpw		0.95	1.0	1.05	ms
Additional program pulse width	twL2	topw		2.85		78.75	ms
$Address \to data \ output \ time$	tdaod	tacc	OE = VIL			2	μs
$\overline{\text{OE}} \downarrow o$ data output time	tDOOD	toe				1	μs
Data hold time (from OE ↑)	thcod	tor		0		130	ns
Data hold time (from address)	t HAOD	tон	OE = VIL	0			ns

Note Corresponding μ PD27C256A symbols.



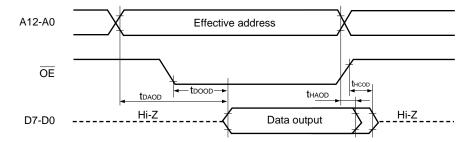
PROM Write Mode Timing



Cautions 1. Apply VDDP before VPP and remove it after VPP.

2. VPP must not exceed +13 V, including the overshoot.

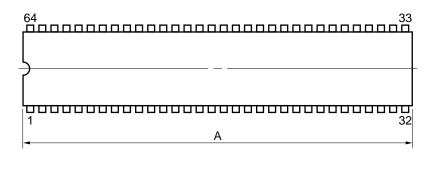
PROM Read Mode Timing

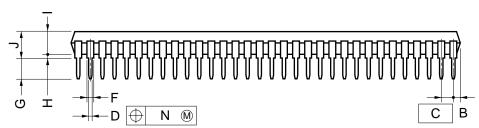


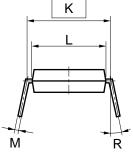


8. PACKAGE DRAWINGS

64 PIN PLASTIC SHRINK DIP (750 mil)







NOTE

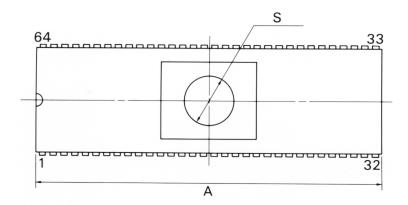
- Each lead centerline is located within 0.17 mm (0.007 inch) of its true position (T.P.) at maximum material condition.
- 2) Item "K" to center of leads when formed parallel.

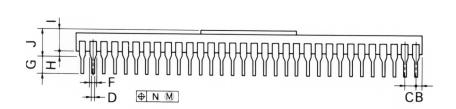
ITEM	MILLIMETERS	INCHES
Α	58.68 MAX.	2.311 MAX.
В	1.78 MAX.	0.070 MAX.
С	1.778 (T.P.)	0.070 (T.P.)
D	0.50±0.10	$0.020^{+0.004}_{-0.005}$
F	0.9 MIN.	0.035 MIN.
G	3.2±0.3	0.126±0.012
Н	0.51 MIN.	0.020 MIN.
I	4.31 MAX.	0.170 MAX.
J	5.08 MAX.	0.200 MAX.
K	19.05 (T.P.)	0.750 (T.P.)
L	17.0	0.669
М	0.25 ^{+0.10} -0.05	0.010+0.004
N	0.17	0.007
R	0~15°	0~15°

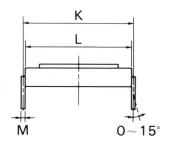
P64C-70-750A,C-1



64PIN CERAMIC SHRINK DIP (750 mil)







P64DW-70-750A

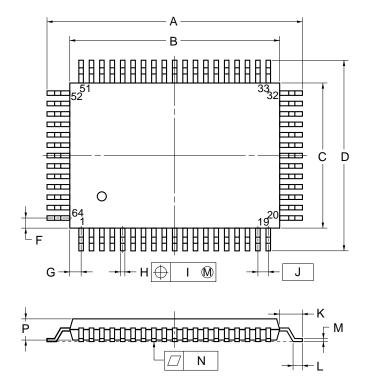
NOTES

- Each lead centerline is located within 0.25 mm (0.01 inch) of its true position (T.P.) at maximum material condition.
- 2) Item "K" to center of leads when formed parallel.

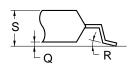
ITEM	MILLIMETERS	INCHES
Α	58.68 MAX.	2.310 MAX.
В	1.78 MAX.	0.070 MAX.
С	1.778 (T.P.)	0.070 (T.P.)
D	0.46 ^{±0.05}	0.018 ±0.002
F	0.8 MIN.	0.031 MIN.
G	3.5 ^{±0.3}	0.138 ^{±0.012}
Н	1.0 MIN.	0.039 MIN.
ı	3.0	0.118
J	5.08 MAX.	0.200 MAX.
К	19.05 (T.P.)	0.750 (T.P.)
L	18.8	0.740
М	0.25 ^{±0.05}	0.010 +0.002 -0.003
N	0.25	0.01
S	φ 8.89	φ 0.350



64 PIN PLASTIC QFP (14×20)



detail of lead end



NOTE

Each lead centerline is located within 0.20 mm (0.008 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
Α	23.6±0.4	0.929±0.016
В	20.0±0.2	0.795+0.008
С	14.0±0.2	0.551+0.009
D	17.6±0.4	0.693±0.016
F	1.0	0.039
G	1.0	0.039
Н	0.40±0.10	$0.016^{+0.004}_{-0.005}$
ı	0.20	0.008
J	1.0 (T.P.)	0.039 (T.P)
K	1.8±0.2	$0.071^{+0.008}_{-0.009}$
L	0.8±0.2	0.031+0.009
М	$0.15^{+0.10}_{-0.05}$	$0.006^{+0.004}_{-0.003}$
N	0.10	0.004
Р	2.7	0.106
Q	0.1±0.1	0.004±0.004
R	5°±5°	5°±5°
S	3.0 MAX.	0.119 MAX.

P64GF-100-3B8,3BE,3BR-2



9. RECOMMENDED SOLDERING CONDITIONS

*

It is recommended that this device be soldered under the following conditions.

For details on the recommended soldering conditions, refer to information document "Semiconductor Devices Mounting Technology Manual" (IEI-1207).

For soldering methods and conditions other than those recommended, please contact your NEC sales representative.

Table 9-1. Soldering Conditions for Surface Mount Devices

μ PD78P328GF-3BE: 64-pin plastic QFP (14 x 20 mm)

Soldering Method	Soldering Conditions	Recommended Soldering
		Code
Infrared reflow	Package peak temperature: 235°C,	IR35-207-2
	Time: 30 seconds max. (210°C min.),	
	Number of times: 2 max, Maximum number of days: 7 days ^{Note}	
	(thereafter, 20 hours of prebaking is required at 125°C)	
	< Cautions >	
	(1) Wait for the device temperature to return to normal after the first	
	reflow before starting the second reflow.	
	(2) Do not perform flux cleaning with water after the first reflow.	
VPS	Package peak temperature: 215°C,	VP15-207-2
	Time: 40 seconds max. (200°C min.),	
	Number of times: 2 max, Maximum number of days: 7 days ^{Note}	
	(thereafter, 20 hours of prebaking is required at 125°C)	
	< Cautions >	
	(1) Wait for the device temperature to return to normal after the first	
	reflow before starting the second reflow.	
	(2) Do not perform flux cleaning with water after the first reflow.	
Wave soldering	Soldering bath temperature: 260°C max., Time: 10 seconds max.,	WS60-207-1
	Number of times: 1,	
	Preheating temperature: 120°C max. (package surface temperature),	
	Maximum number of days: 7 days ^{Note} (thereafter, 20 hours of	
	prebaking is required at 125°C).	
Partial heating	Pin temperature: 300°C max.,	_
	Time: 3 seconds max. (per pin row)	

Note Number of days after unpacking the dry pack. Storage conditions are 25°C and 65% RH max.

Caution Do not use different soldering methods together (except the partial heating method).

Table 9-2. Soldering Conditions for Through-hole Devices

 μ PD78P328CW: 64-pin Plastic Shrink DIP (750 mils)

 μ PD78P328DW: 64-pin Ceramic Shrink DIP (750 mils) (with window)

Soldering Method	Soldering Conditions
Wave soldering (pin only)	Soldering bath temperature: 260°C max., Time: 10 seconds max.
Partial heating	Pin temperature: 300°C max., Time: 3 seconds max. (per pin)

Caution Apply wave soldering only to the pins and be careful so as not to bring solder into direct contact with the package.

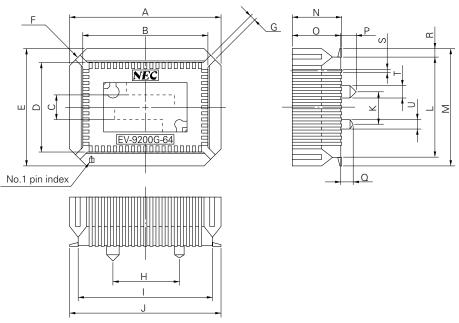


APPENDIX A. DRAWINGS OF CONVERSION SOCKET AND RECOMMENDED FOOTPRINT

The emulation probe (EP-78327GF-R) for the μ PD78P328GF-3BE is connected with the target system in combination with the conversion socket (EV-9200G-64).

The drawings of the socket and recommended footprint are shown below.

Figure A-1. Drawing of Conversion Socket (EV-9200G-64) (for reference only)



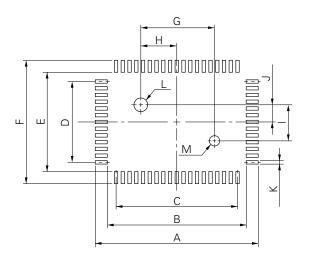
EV-9200G-64-G0

ITEM	MILLIMETERS	INCHES
А	25.0	0.984
В	20.30	0.799
С	4.0	0.157
D	14.45	0.569
Е	19.0	0.748
F	4-C 2.8	4-C 0.11
G	0.8	0.031
I	11.0	0.433
	22.0	0.866
J	24.7	0.972
K	5.0	0.197
L	16.2	0.638
М	18.9	0.744
0	8.0	0.315
Ν	7.8	0.307
Р	2.5	0.098
Q	2.0	0.079
R	1.35	0.053
S	0.35±0.1	0.014 ^{+0.004} _{-0.005}
Т	ø2.3	ø0.091
U	ø 1.5	φ0.059





Figure A-2. Recommended Footprint for EV-9200G-64 (for reference only)



EV-9200G-64-P0

ITEM	MILLIMETERS	INCHES
А	25.7	1.012
В	21.0	0.827
С	1.0±0.02 × 18=18.0±0.05	$0.039^{+0.002}_{-0.001} \times 0.709 = 0.709^{+0.002}_{-0.003}$
D	$1.0\pm0.02 \times 12=12.0\pm0.05$	$0.039^{+0.002}_{-0.001} \times 0.472 = 0.472^{+0.003}_{-0.002}$
Е	15.2	0.598
F	19.9	0.783
G	11.00±0.08	$0.433^{+0.004}_{-0.003}$
Н	5.50±0.03	0.217 ^{+0.001} _{-0.002}
- 1	5.00±0.08	0.197 ^{+0.003} _{-0.004}
J	2.50±0.03	0.098 ^{+0.002} _{-0.001}
K	0.6±0.02	0.024 ^{+0.001} _{-0.002}
L	φ2.36±0.03	φ0.093 ^{+0.001} _{-0.002}
М	φ1.57±0.03	φ0.062 ^{+0.001} _{-0.002}

Caution Dimensions of mount pad for EV-9200 and that for target device (QFP) may be different in some parts. For the recommended mount pad dimensions for QFP, refer to "SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL" (IEI-1207).





* APPENDIX B. TOOLS

B.1 Development Tools

The following development tools are readily available to support development of systems using the μ PD78P328:

Language Processor

78K/III Series	Relocatable assembler common to the 78K/III series. Since it contains the macro function, the					
relocatable assembler	development efficiency can be improved. A structured assembler which enables you to explicity					
(RA78K/III)	describe program control structure is also attached and program productivity and maintenance					
	can be improved.					
	Host machine			Ordering code		
		os	Supply medium	(product name)		
	PC-9800 series	MS-DOS™	3.5-inch 2HD	μS5A13RA78K3		
			5-inch 2HD	μS5A10RA78K3		
	IBM PC/AT™	PC DOS™	3.5-inch 2HC	μS7B13RA78K3		
	and compatible machine		5-inch 2HC	μS7B10RA78K3		
	HP9000 series 700™	HP-UX™	DAT	μS3P16RA78K3		
	SPARCstation TM SunOS TM Cartridge tape μ S3K15RA78K3					
	NEWS™	NEWS-OS™	(QIC-24)	μS3R15RA78K3		
78K/III Series	C compiler common to the	e 78K/III series. Th	is is a program to convert	a program written in C		
C compiler	language into an object co	ode executable with	a microcontroller. When	using the compiler,		
(CC78K/III)	78K/III series relocatable	assembler(RA78K/I	III) is necessary.			
	Host machine			Ordering code		
		os	Supply medium	(product name)		
	PC-9800 series	MS-DOS	3.5-inch 2HD	μS5A13CC78K3		
			5-inch 2HD	μS5A10CC78K3		
	IBM PC/AT™	PC DOS	3.5-inch 2HC	μS7B13CC78K3		
	and compatible machine		5-inch 2HC	μS7B10CC78K3		
	HP9000 series 700	HP-UX	DAT	μS3P16CC78K3		
	SPARCstation	SunOS	Cartridge tape	μS3K15CC78K3		
	NEWS	NEWS-OS	(QIC-24)	μS3R15CC78K3		

Remark The operation of the relocatable assembler and C compiler is guaranteed only on the host machine under the operating systems listed above.





PROM Write Tools

Hard-	PG-1500	PG-1500 is a PROM programmer which enables you to program single chip micro-			
ware		controllers containing PROM by stand-alone or host machine operation by connecting an			
		attached board and option	nal programmer adapt	er to PG-1500. It also	enables you to
		program typical PROM de	evices of 256K bits to	4M bits.	
	UNISITE	PROM programmer manu	ufactured by Data I. O.	Japan.	
	2900				
	PA-78P328CW	PROM programmer adap	ters to write programs	onto the μ PD78P328 (on a general
	PA-78P328GF	purpose PROM programn	ner such as PG-1500.		
		PA-78P328CW μPD78P328CW and 78P328DW			
		PA-78P328GF μPD78	P328GF		
Soft-	PG-1500 controller	Connects PG-1500 and a	host machine by a se	rial or parallel interface	and controlls
ware		PG-1500 on the host mad	chine.		
		Host machine			Ordering code
			os	Supply medium	(product name)
	PC-9800 series MS-DOS 3.5-inch 2HD				μS5A13PG1500
				5-inch 2HD	μS5A10PG1500
		IBM PC/AT	PC DOS	3.5-inch 2HD	μS7B13PG1500
		and compatible machine		5-inch 2HC	μS7B10PG1500

Remark The operation of the PG-1500 controller is guaranteed only on the host machine under the operating systems listed above.

Debugging Tools

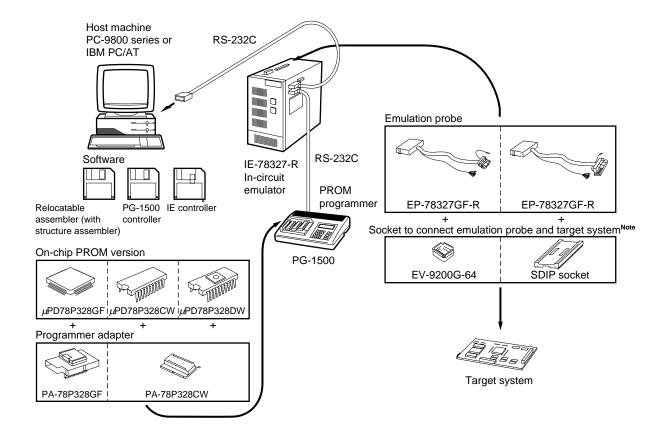
Hard-	- IE-78327-R		IE-78327-R is an in-circuit emulator that can be used for application system development				
ware	е		and debugging.	and debugging.			
	EP-78327CW-R		Emulation probe for 64-pir	n plastic shrink DIP to	connect IE-78327-R to	the target system.	
	EP-78327GF	-R	Emulation probe for 94-pir	Emulation probe for 94-pin plastic QFP to connect IE-78327-R to the target system.			
		EV-9200G-64	One conversion socket E\	/-9200G-64 used for c	connection to the target	system	
			is attached.				
Soft-	IE-78327-R		Program to control IE-78327-R on a host machine. Automatic execution of commands,				
ware	control progi	am	etc., is enabled for more efficient debugging.				
	(IE controlle	r)	Host machine	Host machine Ord		Ordering code	
				os	Supply medium	(product name)	
			PC-9800 series	MS-DOS	3.5-inch 2HD	μS5A13IE78327	
					5-inch 2HD	μS5A10IE78327	
			IBM PC/AT	PC DOS	3.5-inch 2HD	μS7B13IE78327	
			and compatible machine		5-inch 2HC	μS7B10IE78327	

Remark The operation of the IE controller is guaranteed only on the host machine under the operating systems listed above.





Development Tool Configuration



Note The socket is attached to the emulation probe.

- Remarks 1. The host machine and PG-1500 can be connected directly by RS-232-C.
 - 2. Supply media of software are represented as 3.5-inch floppy disks in the figure above.





B.2 Evaluation Tools

The following evaluation tools are provided to evaluate the μ PD78P328 function:

Ordering Code	Host Machine	Function
(product name)		
EB-78327-98	PC-9800 series	The μ PD78P328 function can be easily evaluated by connecting the evaluation tool to
		a host machine. The EB-78327-98/PC command system basically is compliant with the
EB-78327-PC	IBM PC/AT	IE-78327-R command system. Thus, easy transition to application system development
	and compatible	process by IE-78327-R can be made. The evaluation tools enable turbo access manager
	machine	(μPD71P301) ^{Note} to be mounted on the printed circuit board.

Note Turbo access manager (μ PD71P301) is available for maintenance purpose only.

Cautions 1. EB-78327-98/PC is not the μ PD78P328 application system development tool.

2. EB-78327-98/PC does not contain the emulation function at internal PROM execution of the μ PD78P328.

B.3 Embedded Software

The following embedded software products are readily available to support more efficient program development and maintenance:

Real-time OS

Real-time OS	The purpose of RX78	The purpose of RX78K/III is to realize a multi-task environment in a control area which requires				
(RX78K/III)	real-time processing.	real-time processing. RX78K/III allocates idle times of CPU to other processing to improve				
	overall performance of	overall performance of the system.				
	RX78K/III provides a	system call based on	the μ ITRON specification.			
	RX78K/III assembler	package provides the	RX78K/III nucleus and a to	ol (configurator) to		
	prepare multiple information tables.					
	Host machine			Ordering code		
		OS	Supply medium	(product name)		
	PC-9800 series	MS-DOS	3.5-inch 2HD	μS5A13RX78320		
			5-inch 2HD	μS5A10RX78320		
	IBM PC/AT PC DOS 3.5-inch 2HC μS7B13RX783					
	and compatible mach	ine	5-inch 2HC	μS7B10RX78320		

Caution When purchasing the RX78K/III, fill in the purchase application form in advance, and sign the User's Agreement.

Remark When using the RX78K/III Real-time OS, the RA78K/III assembler package (option) is necessary.





Fuzzy Inference Development Support System

Fuzzy knowledge Data	Program supporting input of fuzzy knowledge data (fuzzy rule and membership function),				
Preparation Tool	input/editing (edit), and evaluation (simulation).				
(FE9000, FE9200)					
,	Host machine				Ordering code
		OS		Supply medium	(product name)
	PC-9800 series	MS-DOS		3.5-inch 2HD	μS5A13FE9000
				5-inch 2HD	μS5A10FE9000
	IBM PC/AT	PC DOS	Windows™	3.5-inch 2HC	μS7B13FE9200
	and compatible machine			5-inch 2HC	μS7B10FE9200
Translator	Program converting fuzzy knowledge data obtained by using fuzzy knowledge data preparate				
(FT78K3)Note	tool to the assembler source program for the RA78K/III.				
	Host machine				Ordering code
		OS		Supply medium	(product name)
	PC-9800 series	MS-DOS		3.5-inch 2HD	μS5A13FT78K3
				5-inch 2HD	μS5A10FT78K3
	IBM PC/AT	PC DOS		3.5-inch 2HC	μS7B13FT78K3
	and compatible machine			5-inch 2HC	μS7B10FT78K3
Fuzzy Inference Module	Program executing fuzzy inference. Fuzzy inference is executed by linking fuzzy knowled				
(FI78K/III) ^{Note}	data converted by translator.				
	Host machine				Ordering code
		OS		Supply medium	(product name)
	PC-9800 series	MS-DOS		3.5-inch 2HD	μS5A13FI78K3
				5-inch 2HD	μS5A10FI78K3
	IBM PC/AT	PC DOS		3.5-inch 2HC	μS7B13FI78K3
	and compatible machine			5-inch 2HC	μS7B10FI78K3
Fuzzy Inference Debugger	ce Debugger Support software evaluating and adjusting fuzzy knowledge data at hardware level by using				
(FD78K/III)	in-circuit emulator.				
	Host machine				Ordering code
		OS		Supply medium	(product name)
	PC-9800 series	MS-DOS		3.5-inch 2HD	μS5A13FD78K3
				5-inch 2HD	μS5A10FD78K3
	IBM PC/AT	PC DOS		3.5-inch 2HC	μS7B13FD78K3
	and compatible machine	compatible machine		5-inch 2HC	μS7B10FD78K3

Note Under development



[MEMO]

Note:



NOTES FOR CMOS DEVICES

(1) PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

(2) HANDLING OF UNUSED INPUT PINS FOR CMOS

Note: No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

(3) STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note: Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

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HP9000 series 700 and HP-UX are trademarks of Hewlett-Packard Company.

SPARCstation is a trademark of SPARC International, Inc.

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NEWS and NEWS-OS are trademarks of Sony Corporation.

TRON is an abbreviation of The Realtime Operating system Nucleus.

ITRON is an abbreviation of Industrial TRON.





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License not needed: μPD78P328DW

The customer must judge the need for license: μ PD78P328CW, 78P328GF-3BE

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Standard: Computer, office equipment, communications equipment, test and measurement equipment,

audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment

and industrial robots

Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for

life support)

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